

Absolute maximum ratings

(Ta=25°C)

Symbol	Ratings	Unit
V _{DSS}	200	V
V _{GSS}	±20	V
I _D	±10	A
I _{D(pulse)}	±40 (PW≤1ms, DU≤1%)	A
E _{AS*}	120	mJ
P _T	5 (Ta=25°C, with all circuits operating, without heatsink) 40 (Tc=25°C, with all circuits operating, with infinite heatsink)	W
θ _{j-a}	25 (Junction-Air, Ta=25°C, with all circuits operating)	°C/W
θ _{j-c}	3.13 (Junction-Case, Tc=25°C, with all circuits operating)	°C/W
V _{iso}	1000 (Between fin and lead pin, AC)	Vrms
T _{ch}	150	°C
T _{tsg}	-40 to +150	°C

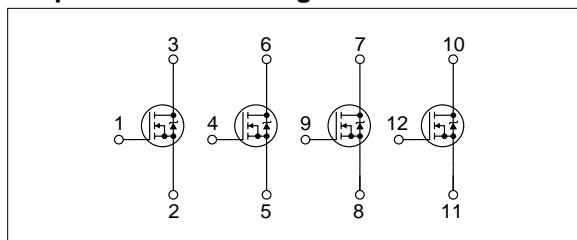
* : V_{DD}=25V, L=2.1mH, I_D=10A, unclamped, R_G=50Ω, see Fig. E on page 15.

Electrical characteristics

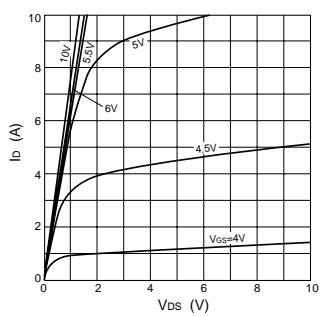
(Ta=25°C)

Symbol	Specification			Unit	Conditions
	min	typ	max		
V _{(BR)DSS}	200			V	I _D =100μA, V _{GS} =0V
I _{GSS}			±100	nA	V _{GS} =±20V
I _{DSS}			100	μA	V _{DS} =200V, V _{GS} =0V
V _{TH}	2.0		4.0	V	V _{DS} =10V, I _D =1mA
R _{e(yfs)}	5.0	8.5		S	V _{DS} =10V, I _D =5A
R _{Ds(ON)}		130	175	mΩ	V _{GS} =10V, I _D =5A
C _{iss}		850		pF	V _{DS} =10V, f=1.0MHz, V _{GS} =0V
C _{oss}		550		pF	
t _{d(on)}		20		ns	I _D =5A, V _{DD} =100V, R _L =20Ω, V _{GS} =10V, see Fig. 3 on page 16.
t _r		25		ns	
t _{d(off)}		70		ns	
t _f		70		ns	
V _{SD}		1.0	1.5	V	I _D =10A, V _{GS} =0V
t _{rr}		500		ns	I _D =±100mA

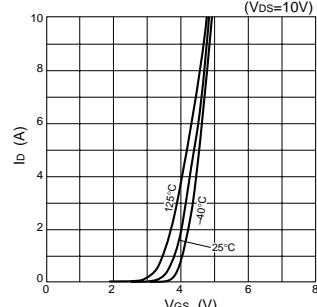
Equivalent circuit diagram



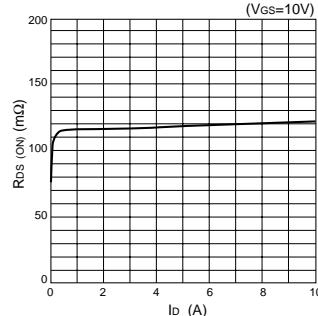
I_D-V_{DS} Characteristics (Typical)



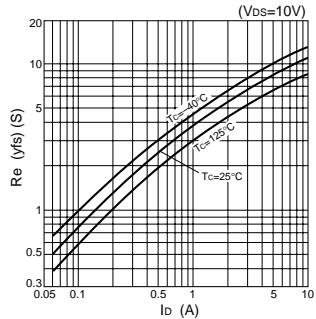
I_D-V_{GS} Characteristics (Typical)



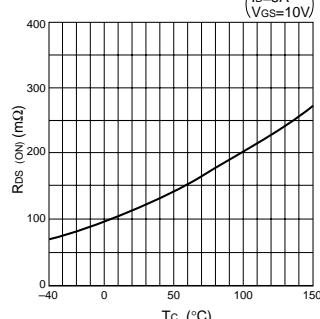
R_{Ds(ON)}-I_D Characteristics (Typical)



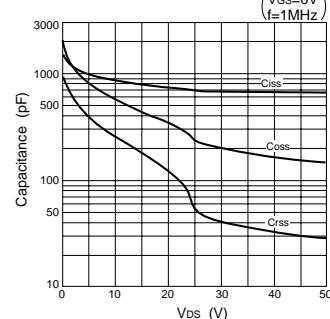
R_{e(yfs)}-I_D Characteristics (Typical)



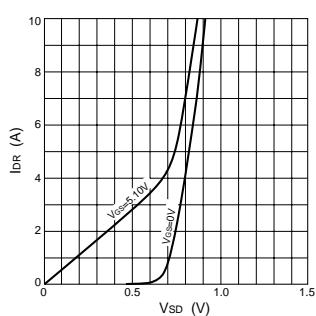
R_{Ds(ON)}-T_c Characteristics (Typical)



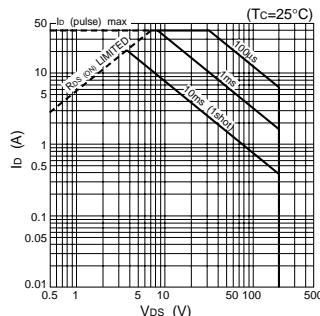
Capacitance-V_{DS} Characteristics (Typical)



I_{DR}-V_{SD} Characteristics (Typical)



Safe Operating Area (SOA)



P_T-T_a Characteristics

